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APPLICATION N	O. F	ILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/021,081		12/19/2001	Dan-Xia Xu	12318-US	8729	
23553	7590	10/03/2003		EXAM	EXAMINER	
MARKS	& CLERK		MULPURI, SAVITRI			
P.O. BOX STATION			ART UNIT	PAPER NUMBER		
OTTAWA	A, ON KIE	P 5S7	2812			
CANADA	1		DATE MAILED: 10/03/2003			

Please find below and/or attached an Office communication concerning this application or proceeding.

Application No.

Applicant(s) 10/021,081

Xu et al

Office Action Summary

Examiner

Savitri Mulpuri

Art Unit 2812



	<u></u>	Outran marpan				
	The MAILING DATE of this communication appears	on the cover sheet with the corres				
Period 1	or Reply					
THE N	ORTENED STATUTORY PERIOD FOR REPLY IS SET MAILING DATE OF THIS COMMUNICATION.					
mailing If the p If NO p Failure Any re	ions of time may be available under the provisions of 37 CFR 1.136 (a). In date of this communication. Beriod for reply specified above is less than thirty (30) days, a reply within the Beriod for reply is specified above, the maximum statutory period will apply to reply within the set or extended period for reply will, by statute, cause to ply received by the Office later than three months after the mailing date of patent term adjustment. See 37 CFR 1.704(b).	the statutory minimum of thirty (30) days will b and will expire SIX (6) MONTHS from the mailin the application to become ABANDONED (35 U.S	e considered timely. ng date of this communication. S.C. § 133).			
Status	•					
1) 💢	Responsive to communication(s) filed on Aug 6, 2	002	·			
2a) 🗌	This action is FINAL . 2b) \square This ac	tion is non-final.				
3) 🗆	Since this application is in condition for allowance closed in accordance with the practice under $\textit{Ex pa}$					
Disposi	tion of Claims					
4) 💢	Claim(s) 6-17	is/are	e pending in the application.			
4	a) Of the above, claim(s)	is/ar	e withdrawn from consideration.			
5) 🗆	Claim(s)		is/are allowed.			
6) 💢	Claim(s) 6-17		is/are rejected.			
7) 🗆	Claim(s)		is/are objected to.			
8) 🗆	Claims	are subject to restric	ction and/or election requirement.			
Applica	tion Papers					
9) 🗆	The specification is objected to by the Examiner.					
10)□	The drawing(s) filed on is/are	e a) \square accepted or b) \square objecte	ed to by the Examiner.			
	Applicant may not request that any objection to the					
11)	The proposed drawing correction filed on		b) ☐ disapproved by the Examiner.			
	If approved, corrected drawings are required in reply	to this Office action.				
12)	The oath or declaration is objected to by the Exam	niner.				
Priority under 35 U.S.C. §§ 119 and 120						
	Acknowledgement is made of a claim for foreign p	priority under 35 U.S.C. § 119(a)	(σ) or (τ).			
a) ∟	☐ All b)☐ Some* c)☐ None of:					
	1. ☐ Certified copies of the priority documents ha		Ja			
	2. Certified copies of the priority documents ha					
*S	 Copies of the certified copies of the priority of application from the International Burdee the attached detailed Office action for a list of the 	eau (PCT Rule 17.2(a)).	this National Stage			
14)	Acknowledgement is made of a claim for domestic	c priority under 35 U.S.C. § 119	(e).			
a)[The translation of the foreign language provision	al application has been received.				
15)□	Acknowledgement is made of a claim for domestic	c priority under 35 U.S.C. §§ 12	0 and/or 121.			
Attachm	ent(s)					
1) 💢 No	otice of References Cited (PTO-892)	4) Interview Summary (PTO-413) Paper				
	otice of Draftsperson's Patent Drawing Review (PTO-948)	5) Notice of Informal Patent Application	(PTO-152)			
3) 💢 In	formation Disclosure Statement(s) (PTO-1449) Paper No(s). 2,3	6) Other:				

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DETAILED ACTION

This action is in response to the election of process claims 6-17, filed on 8/6/03.

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 6-17 are rejected under 35 U.S.C. 103(a) as being unpatentable over Manta et al.

Manta discloses a method of making several devices including photo detector and waveguides by the following process steps: providing a SOI substrate; forming a cobalt silicide layer on the silicon layer of SOI structure (see fig 1(b) i.e., bottom figure with SOI structure); patterning the silicide layer. Forming Si mesa structures (I, II, III) surrounded by silicide (see fig 1b and fig. 9). Manta et al discloses forming silicon islands surrounded by silicide becomes waveguide, wherein the refractive index jump at the boundary between silicide and silicon enable the transmission and light in the waveguide, which is similar to forming silicide surrounding the silicon as mirror in the instant invention. Manta et al also discloses forming Si/SiGe superlatticess as an alternative to the just silicon layer alone for making a device (see fig. 8 and

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col. 9, lines 35-57). Manta et al discloses forming photo detectors and waveguides(see col.5, lines 10-17).

Mantl et al discloses forming patterned silicide and heat treating step in a single step, which is oxidation step. Oxidation step involves simultaneous heat treating along with patterning of silicide is differs from the individual claimed steps of b and c steps of etching and heat treating. However, Mantl et al also discloses forming patterning and etching silicide layer (see fig. 5 a-5c) to form silicon islands surrounding with silicide for FETs. It would have been obvious to one of ordinary skill in the art to form silicon islands through patterning and etching of silicide because it would be art recognized equivalent process for waveguides.

The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. Prior art teaches integration of waveguide and photodetector..

Any inquiry concerning this communication or earlier communications from the examiner should be directed to S. Mulpuri whose telephone number is 703-305-5184. The examiner can normally be reached on Mon-fri from 8 to 4.30 p.m..

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, John Niebling, can be reached on (703) 308-3325. The fax phone number for the organization where this application or proceeding is assigned is 703-308-7722.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is 703-308-0956.

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SAVITRI MULPURI
PRIMARY EXAMINER